

AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph at page 8, line 19 with the following amended paragraph:

-- Finally, in FIG. 1h, a conductive layer (not shown), such as a doped polysilicon layer, is formed overlying the masking layer 103 and fills the upper portion of the bottle-shaped trench 113 (overlying the trench capacitor 119) by conventional deposition, such as CVD. Next, the conductive layer is etched to leave a portion of the conductive layer 120 only in the bottle-shaped trench 113 to serve as a first wiring layer. Thereafter, the collar insulating layer 112' over the conductive layer 120 is removed, leaving a portion of the collar insulating layer 112".

Another conductive layer (not shown), such as a doped polysilicon layer, is subsequently formed overlying the masking layer 103 and fills the bottle-shaped trench 113. Next, the excess conductive layer over the bottle-shaped trench 113 is removed by polishing, such as CMP, to leave a portion of the conductive layer 122 overlying the first wiring layer 120 in the bottle-shaped trench 113 to serve as a second wiring layer.